

FORWARD INTERNATIONAL ELECTRONICS LTD.

**SEMICONDUCTOR  
TECHNICAL DATA**
**2SA1267**

PNP EPITAXIAL SILICON TRANSISTOR

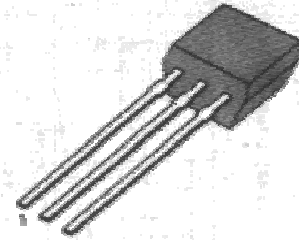
**LOW FREQUENCY AMPLIFIER**

- \* Complement to 2SC3199
- \* Collector-Emitter Voltage  $V_{CE0} = -50V$

**ABSOLUTE MAXIMUM RATINGS at  $T_{amb} = 25^{\circ}C$** 

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	Vcbo	-50	V
Collector-Emitter Voltage	Vceo	-50	V
Emitter-Base Voltage	Vebo	-5	V
Collector Current	Ic	-150	mA
Collector Dissipation	Pc	450	mW
Junction Temperature	Tj	150	$^{\circ}C$
Storage Temperature	Tstg	-55~150	$^{\circ}C$

Package: TO-92S



PIN: STYLE	1	2	3
	E	C	B
NO.1	E	C	B

**ELECTRICAL CHARACTERISTICS at  $T_{amb} = 25^{\circ}C$** 

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BVcbo	-50			V	Ic=-100uA Ie=0
Collector-Emitter Breakdown Voltage	BVceo	-50			V	Ic=-1mA Ib=0
Emitter-Base Breakdown Voltage	BVebo	-5			V	Ie=-100uA Ic=0
Collector Cutoff Current	Icbo			-100	nA	Vcb=-50V Ie=0
DC Current Gain	Hfe	70		400		Vce=-6V Ic=-2mA
Collector-Emitter Saturation Voltage	Vce(sat)			-0.3	V	Ic=-100mA Ib=-10mA
Output Capacitance	Cob			7	pF	Vcb=-10V Ie=0 f=1MHz
Current Gain-Bandwidth Product	fT	80			MHz	Vce=-10V Ic=-1mA

**CLASSIFICATION HFE**

Classification	O	Y	GR
Hfe	70-140	120-240	200-400